## Accepted Manuscript

Title: Influence of growth and annealing temperature on the strain and surface morphology of Ge<sub>995</sub>Sn<sub>0.005</sub> epilayer

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## ACCEPTED MANUSCRIPT

- $Ge_{0.995}Sn_{0.005}$  alloys were grown on Si (100) by MBE at 220~500 °C.
- Surface roughening was enhanced with the increase of growth temperature.
- Non-monotonic temperature dependence of the surface roughening was observed.
- The incorporation of Sn into Ge helped release the residual heteroepitaxial strain.
- The influence of annealing temperature on Ge<sub>0.995</sub>Sn<sub>0.005</sub> was also investigated.

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